

LD6650E4



- Applications
 - Industrial Module

- Special Features

- (1) High optical power with strained multi-quantum well structure.
- (2) Maximum operating temperature of 40 °C.

- Absolute maximum ratings (Tc=25 °C)

Parameter		Symbol	Limit	Unit
Output Power		Po	55	mW
Reverse Voltage	Laser	$V_{R(LD)}$	2	V
	PIN photodiode	$V_{R(PIN)}$	30	V
Operating temperature		Top	-10~+40	
Storage temperature		Tstg	-40~+85	

- Electrical and optical characteristics (Tc=25 °C)

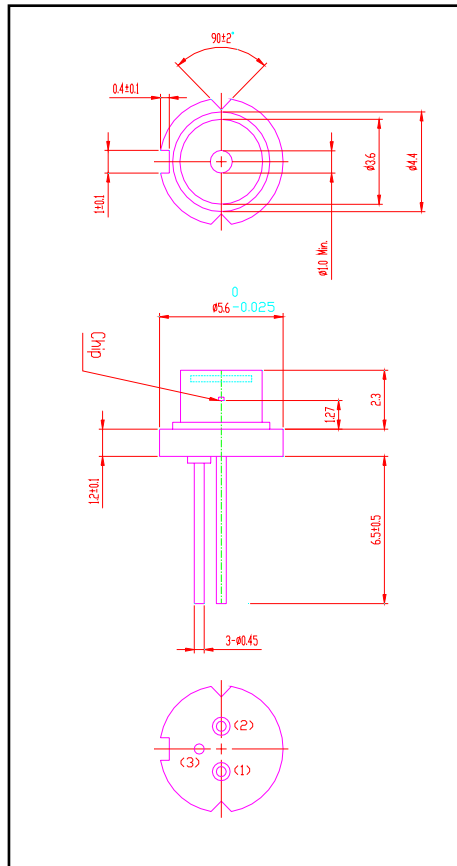
Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Threshold Current	Ith	-	45	70	mA	-
Operating Current	Iop	-	125	150	mA	Po=50mW
Operating Voltage	Vop	-	2.5	3.0	V	Po=50mW
Differential Efficiency		-	0.7	-	mW/mA	Po=30-50mW
Monitor Current	Im	0.05	0.5	2.0	mA	Po=50mW VR(PIN)=5V
Parallel Divergence angle	//*	6	8	12	deg	Po=50mW
Perpendicular Divergence Angle	*	17	22	26	deg	
Parallel Deviation Angle	//	-3	-	+3	deg	
Perpendicular Deviation Angle		-3	-	+3	deg	
Emission Point Accuracy	X Y Z	-80	-	+80	μm	Po=50mW
Peak Wavelength		655	658	666	nm	Po=50mW

* // and * are defined as the angle within which the intensity is 50% of the peak value

- Package and lead configuration please refer to our drawing.
- We can also make per your specification request. Please contact our sales.

Package and Lead Configuration

- Package Drawing: Type A



- Lead Configuration:

